

Abstract of the Disclosure

A method for forming a thermal oxide layer on the surface of a
5 semiconductor substrate exposed during a semiconductor fabricating
process. The thermal oxide layer is to be thin to minimize silicon
substrate defects caused by volume expansion. A chemical vapor
deposition (CVD) layer is then formed on the thin thermal oxide layer,
creating a required thickness. The thin thermal oxide layer and the
10 CVD material layer are formed in the same CVD apparatus. As a result,
a process can be simplified and a particle-leading pollution can be
prevented.